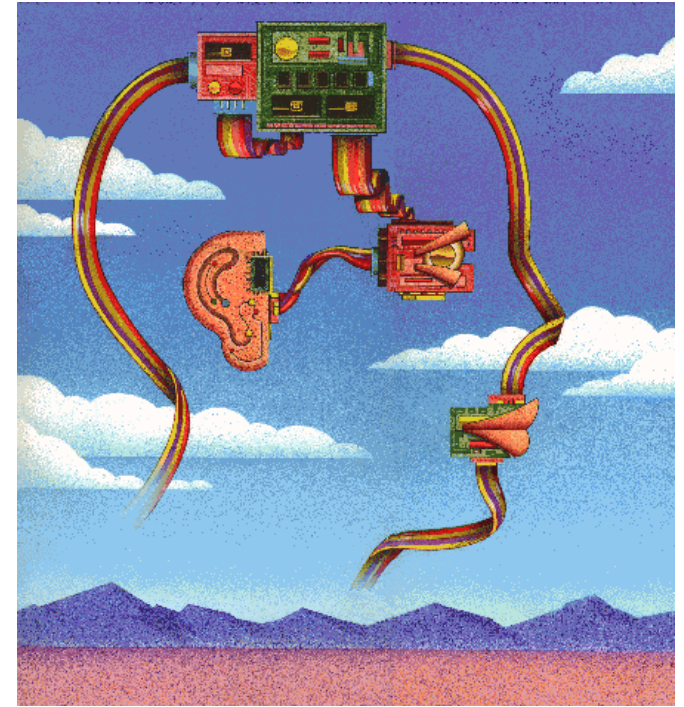


Complex CMOS Gates



Andreas G. Andreou
Pedro Julian

Electrical and Computer Engineering
Johns Hopkins University

<http://andreoulab.net>

Levels of Abstraction –MOS switch and Inverter-

Out = NOT (In)

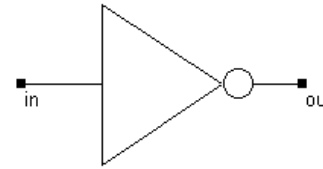
Out = \sim (In)

Equation

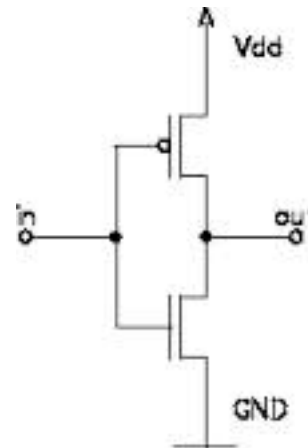
| In | Out |
|----|-----|
| 0 | 1 |
| 1 | 0 |
| X | X |

Truth Table

LOGICAL



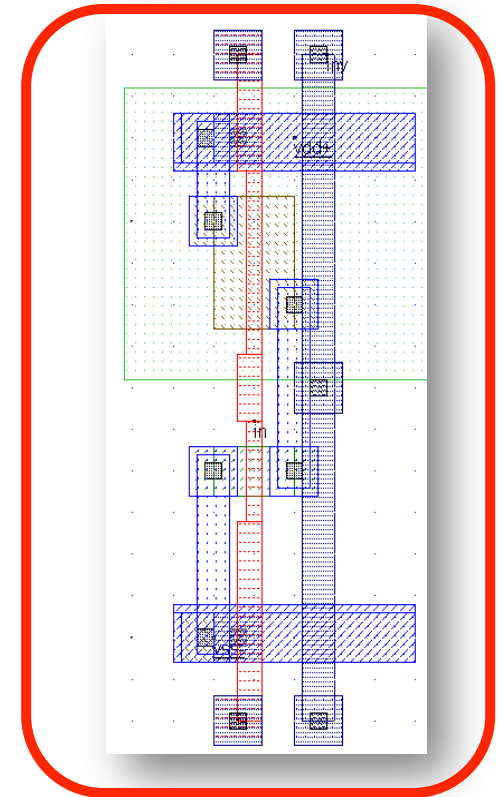
Symbol



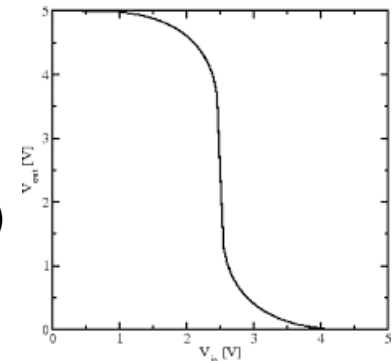
Circuit

Voltage Transfer Characteristics (VTC)

PHYSICAL



Layout

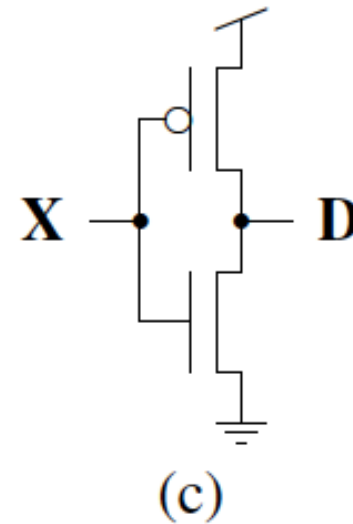
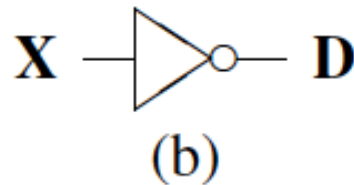


Important rules

- NFET's pull down, PFET's pull up
- Pull up and pull down NOT at the same time
- Output always connected to VDD or GND

| X | D |
|----------|----------|
| 0 | 1 |
| 1 | 0 |

(a)



$$\mathbf{D} = \overline{\mathbf{X}}$$

(d)

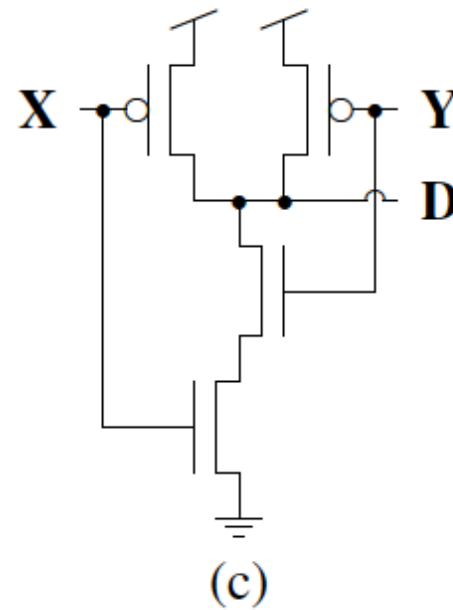
NAND Gate

| Y | X | D |
|----------|----------|----------|
| 0 | 0 | 1 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

(a)



(b)

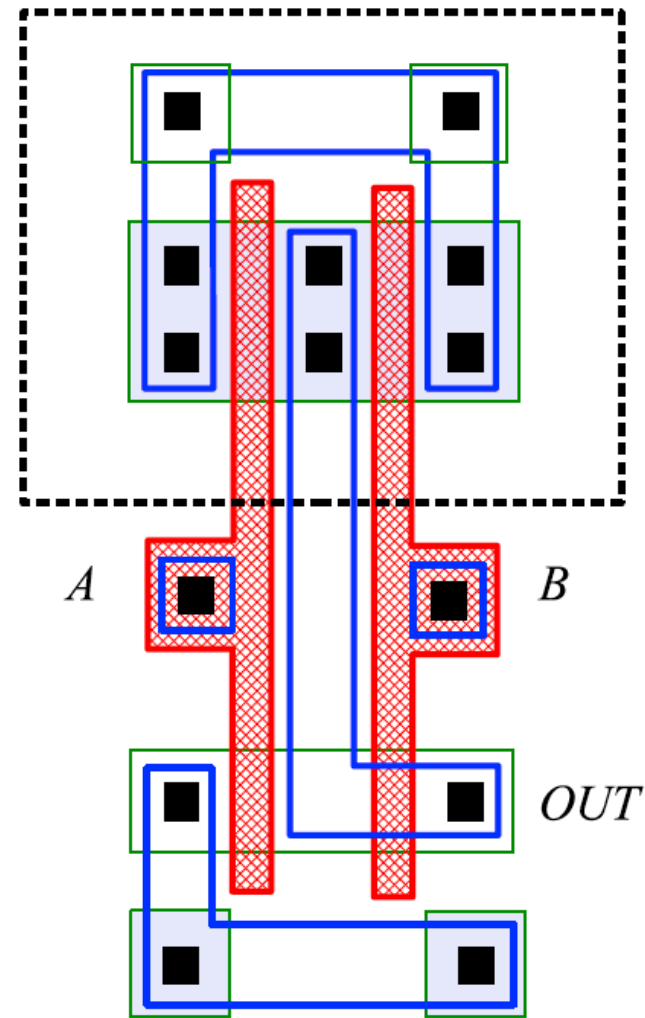
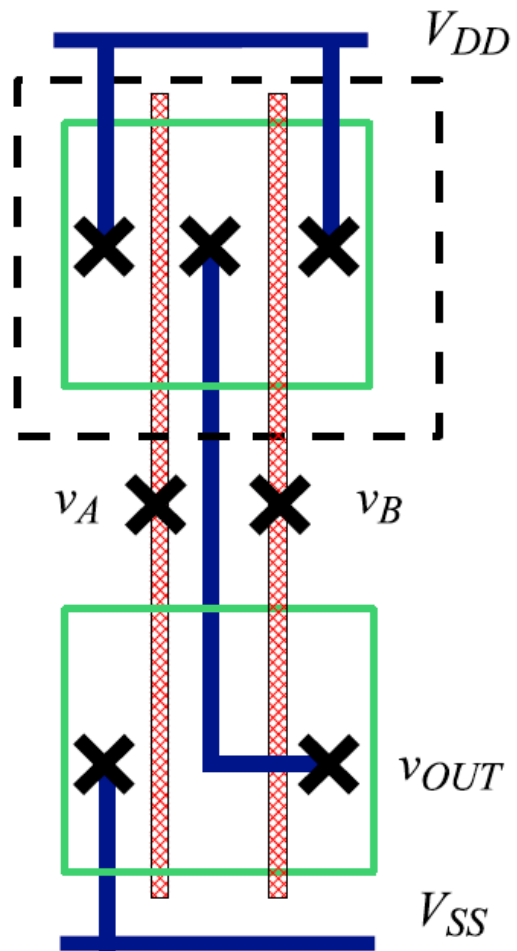


(c)

$$\mathbf{D} = \overline{\mathbf{X} \cdot \mathbf{Y}}$$

(d)

NAND2

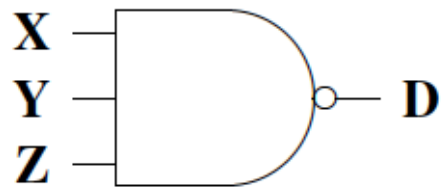


NAND Gate

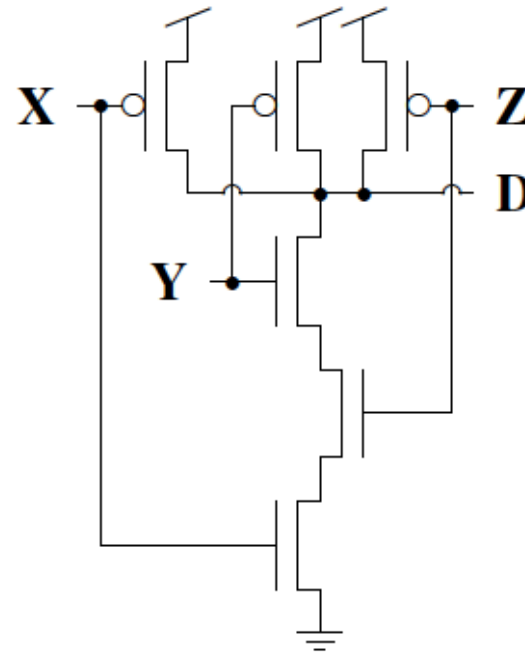
- Three inputs

| Z | Y | X | D |
|----------|----------|----------|----------|
| 0 | 0 | 0 | 1 |
| 0 | 0 | 1 | 1 |
| 0 | 1 | 0 | 1 |
| 0 | 1 | 1 | 1 |
| 1 | 0 | 0 | 1 |
| 1 | 0 | 1 | 1 |
| 1 | 1 | 0 | 1 |
| 1 | 1 | 1 | 0 |

(a)



(b)



(c)

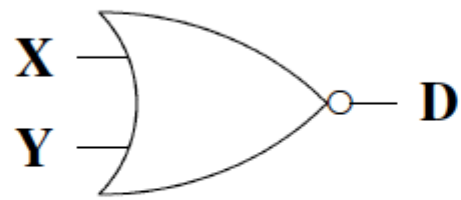
$$\mathbf{D} = \overline{\mathbf{X} \cdot \mathbf{Y} \cdot \mathbf{Z}}$$

(d)

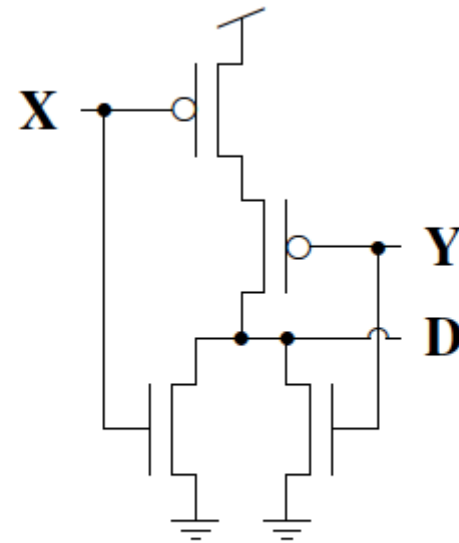
NOR Gate

| Y | X | D |
|----------|----------|----------|
| 0 | 0 | 1 |
| 0 | 1 | 0 |
| 1 | 0 | 0 |
| 1 | 1 | 0 |

(a)



(b)

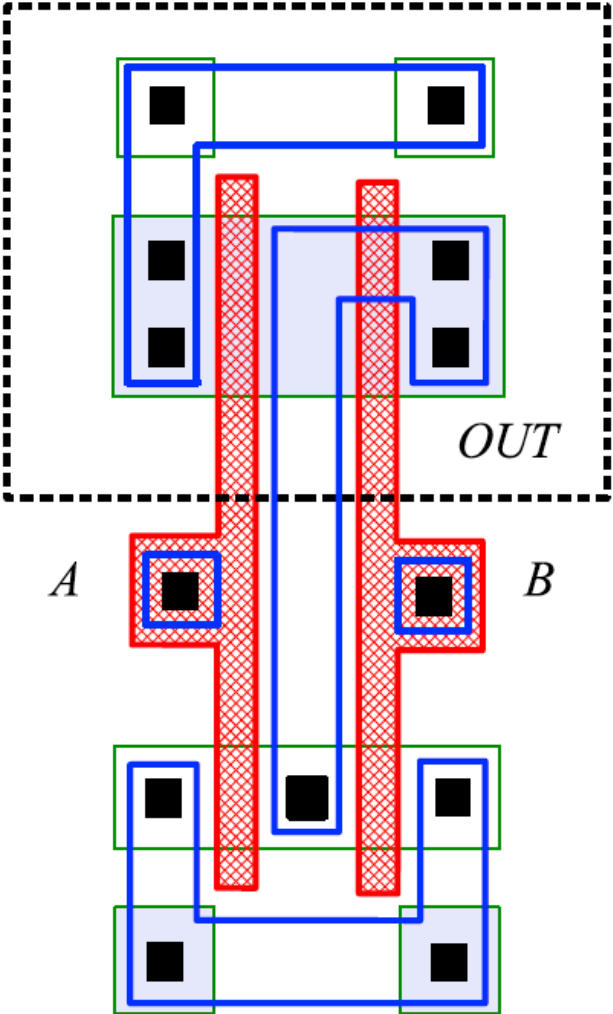
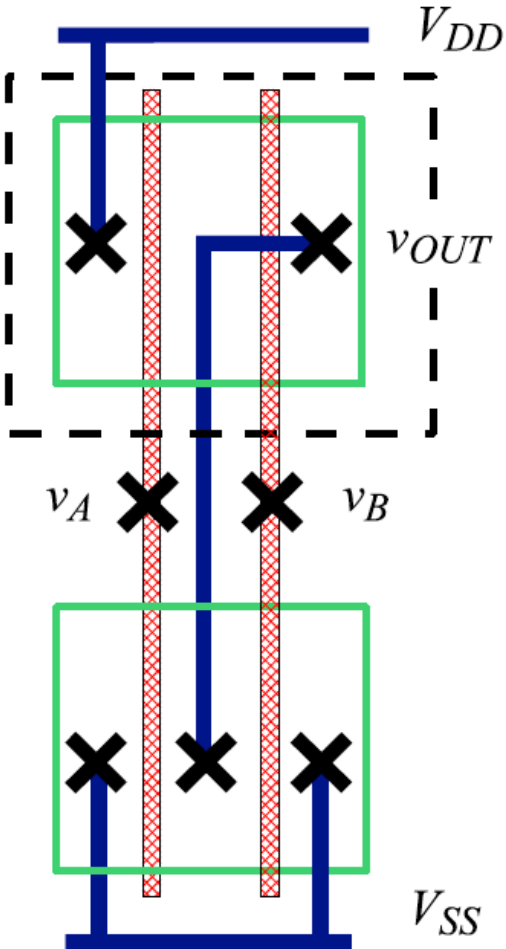


(c)

$$\mathbf{D} = \overline{\mathbf{X} + \mathbf{Y}}$$

(d)

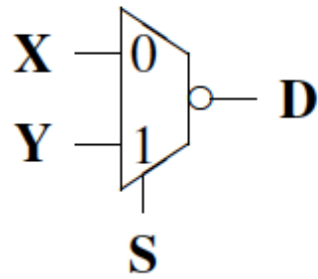
NOR2



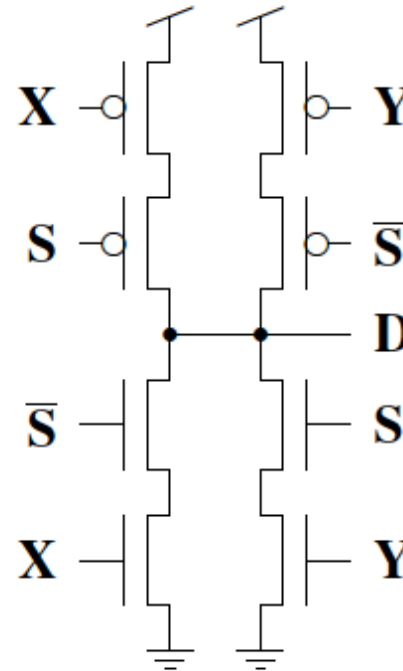
Multiplexer

| S | Y | X | D |
|---|---|---|---|
| 0 | 0 | 0 | 1 |
| 0 | 0 | 1 | 0 |
| 0 | 1 | 0 | 1 |
| 0 | 1 | 1 | 0 |
| 1 | 0 | 0 | 1 |
| 1 | 0 | 1 | 1 |
| 1 | 1 | 0 | 0 |
| 1 | 1 | 1 | 0 |

(a)



(b)



(c)

$$\mathbf{D} = \overline{\mathbf{X} \cdot \overline{\mathbf{S}} + \mathbf{Y} \cdot \mathbf{S}}$$

(d)

Gate Construction

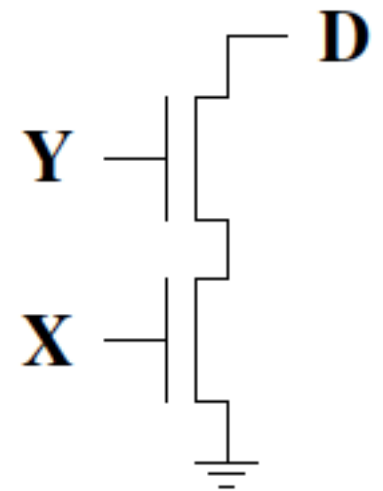
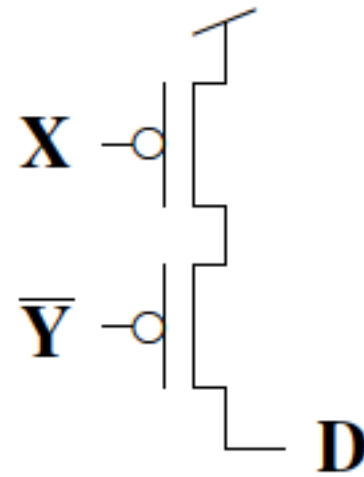
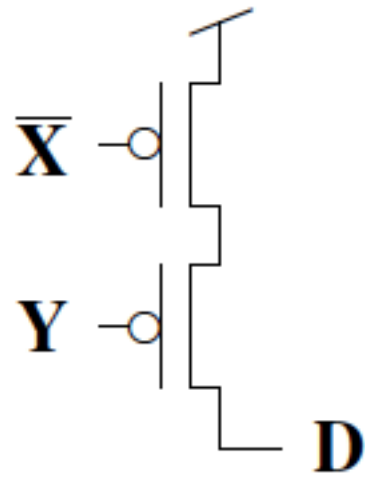
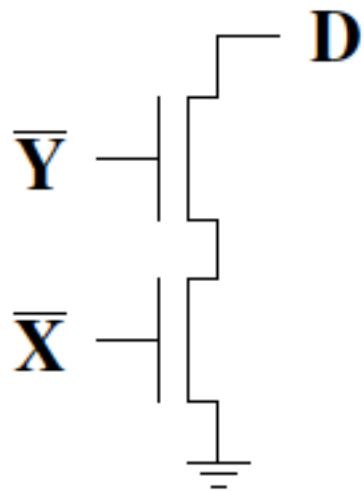
- Truth table method
- Complementary structures

Truth table method

- Example

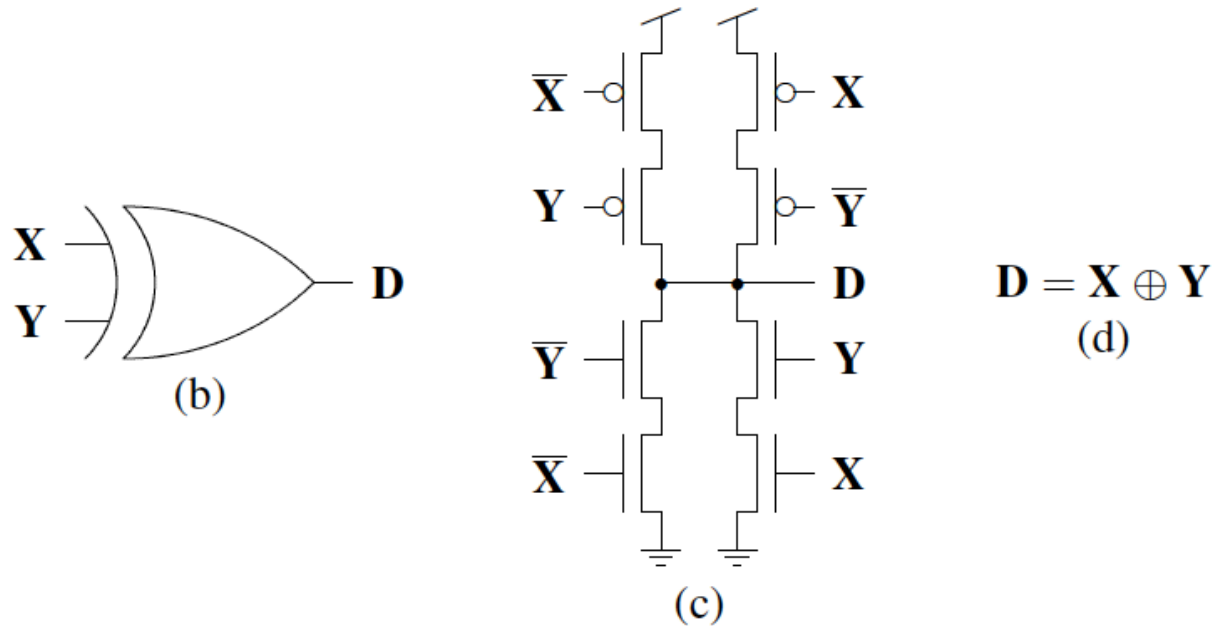
| Y | X | D |
|---|---|---|
| 0 | 0 | 0 |
| 0 | 1 | 1 |
| 1 | 0 | 1 |
| 1 | 1 | 0 |

Line 0
Line 1
Line 2
Line 3



Truth table method

- Result



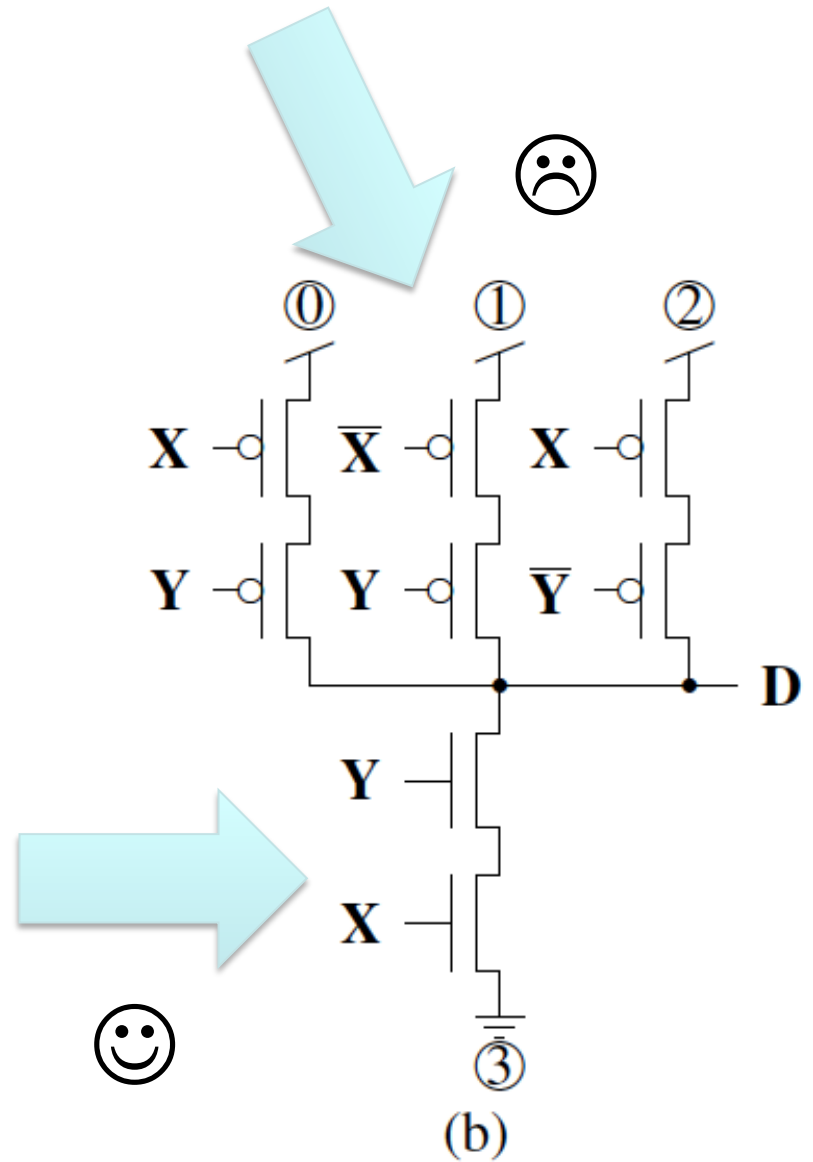
- Disadvantage: n inputs $\rightarrow 2^n$ entries. $2^n \times n$ FETs
- We need inverters to generate \overline{x} and \overline{y}

Truth table method

- NAND gate

| Y | X | D | |
|----------|----------|----------|--------|
| 0 | 0 | 1 | Line 0 |
| 0 | 1 | 1 | Line 1 |
| 1 | 0 | 1 | Line 2 |
| 1 | 1 | 0 | Line 3 |

(a)

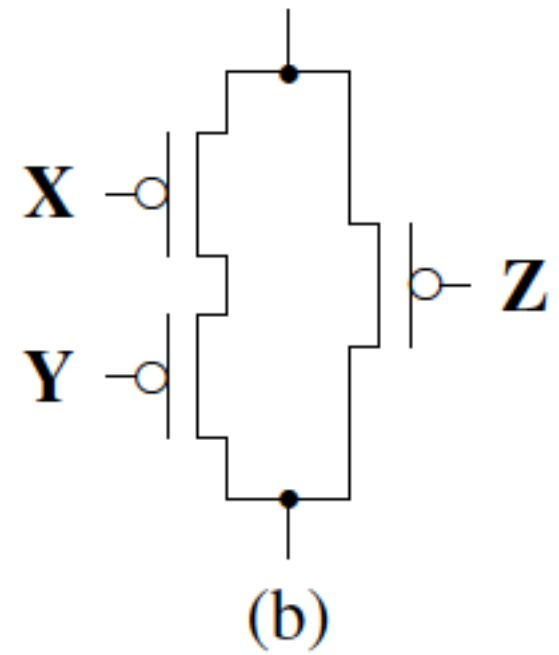
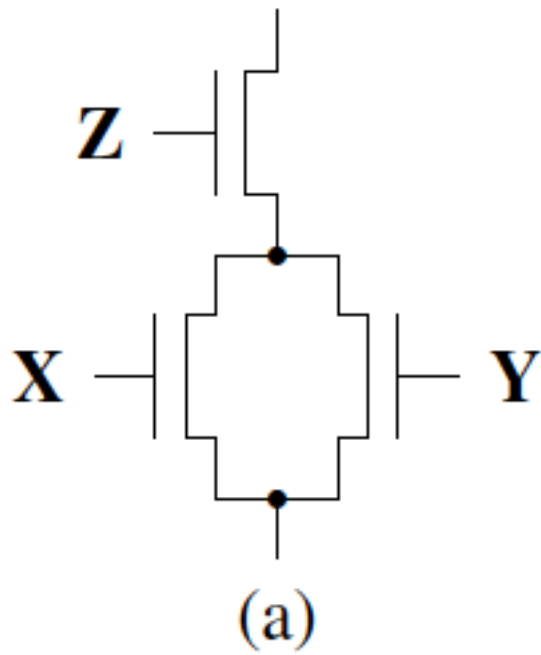


Complementary structures

- Build the PUP from the PDN or viceversa
- Replace
 - PMOS with NMOS (and viceversa)
 - Parallel branches with series branches (and viceversa)
- Signals going to inputs: unchanged

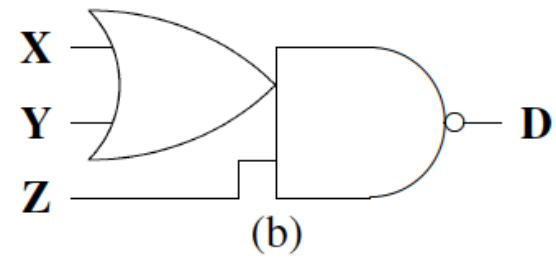
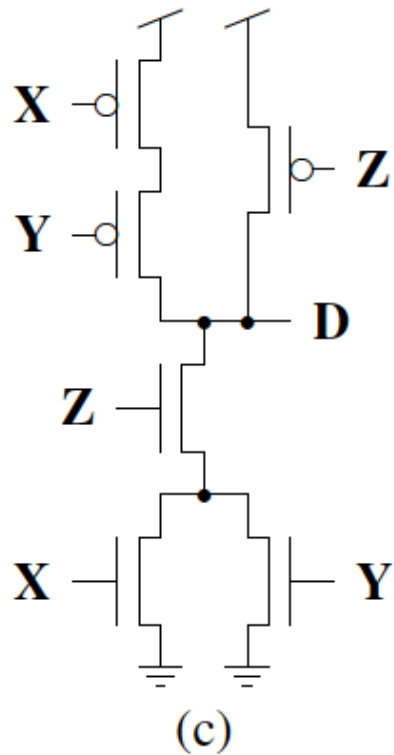
Complementary structures

- Example



Complementary structures

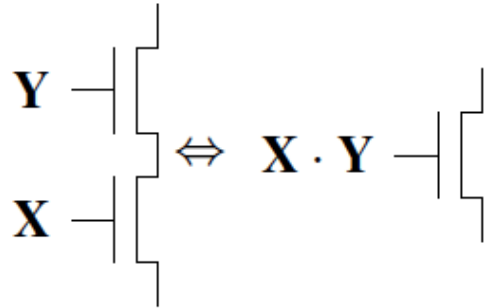
- Example



$$D = \overline{(X + Y)} \cdot Z$$

Boolean equation method (I)

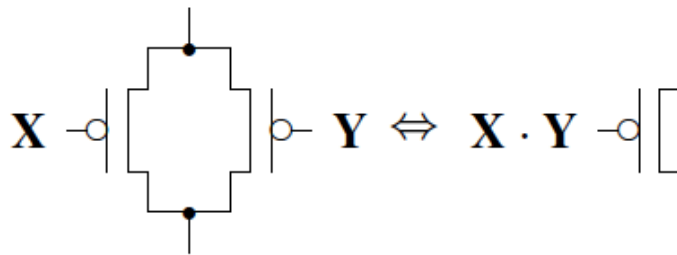
- Any network equivalent to a single FET + Boolean expression



$X=1$ AND $y=1$ then ON

CMOS OUT

$$\overline{x \cdot y}$$

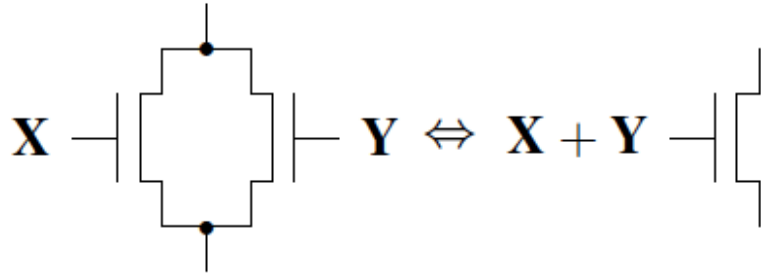


$X=0$ OR $y=0$ then ON

$$\overline{x + y}$$

Boolean equation method (II)

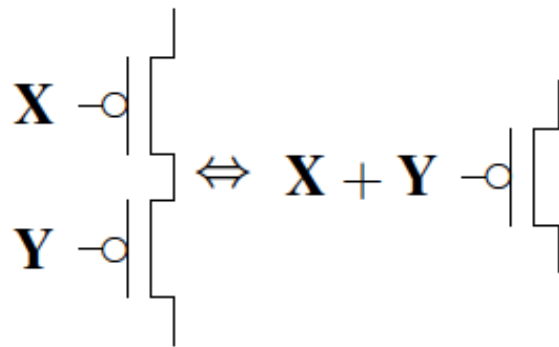
- Any network equivalent to a single FET + Boolean expression



CMOS OUT

$X=1$ OR $y=1$ then ON

$$\overline{x + y}$$

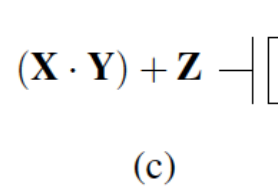
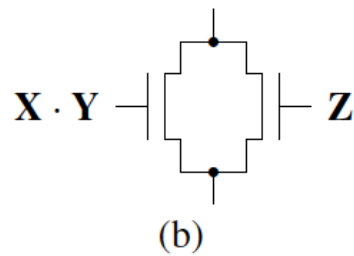
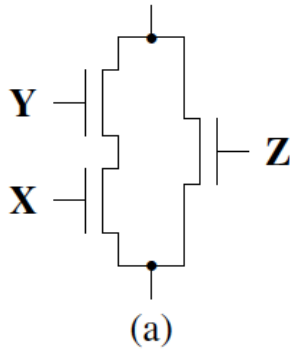


$X=0$ AND $y=0$ then ON

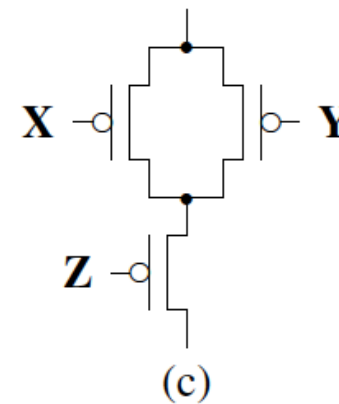
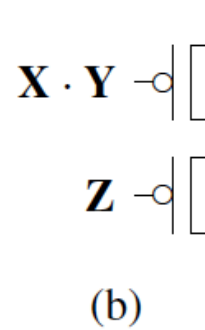
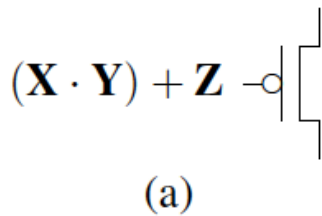
$$\overline{x} \cdot \overline{y}$$

Boolean equation method (I)

- Reduction

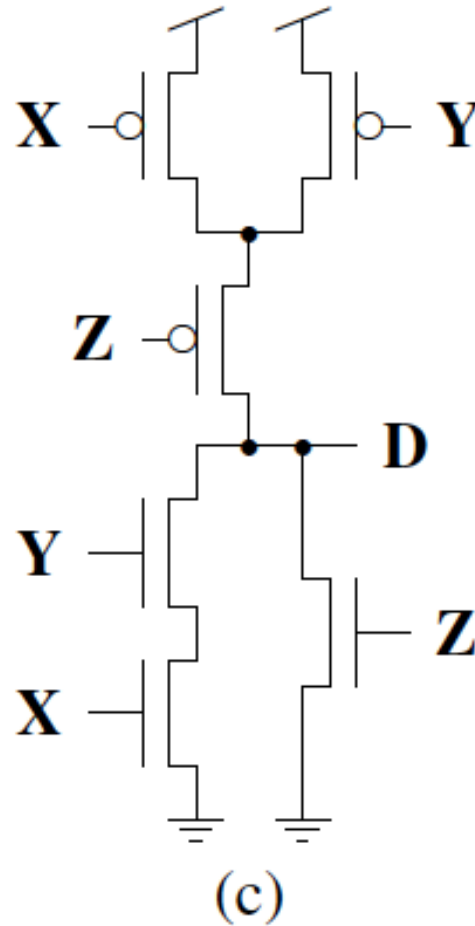


- Expansion



Boolean equation method (II)

- Example



$$\mathbf{D} = \overline{(\mathbf{X} \cdot \mathbf{Y}) + \mathbf{Z}}$$

(d)